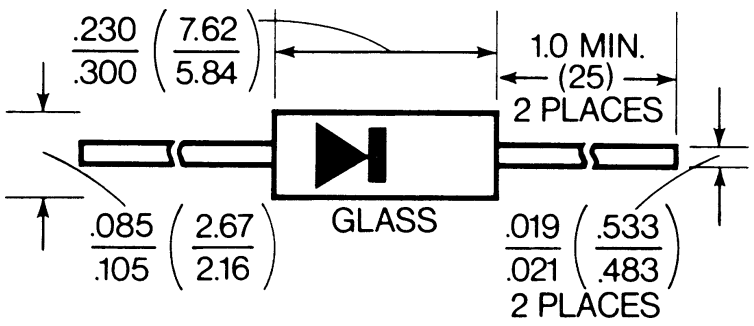
SILICON ABRUPT JUNCTION TUNING VARACTOR

DESCRIPTION:

The **AT6021** is an Epitaxial Silicon Abrupt Junction Microwave Tuning Varactor. This Device is Passivated With Silicon Dioxide Which Results in Very Low Leakage Current. The Capacitance Voltage Relationship Closely Approximates Square Law (n = 0.5).

PACKAGE STYLE 15 (DO-7)



MAXIMUM RATINGS

I_C	100 mA
V_{CE}	70 V
P_{DISS}	250 mW @ T_C = 25 ^{O}C
T_J	-65 to +150 ^{O}C
T_{STG}	-65 to +150 ^{O}C
θ_{JC}	500 ^{O}C/W

CHARACTERISTICS T_C = 25 ^{O}C

SYMBOL	TEST CONDITIONS		MINIMUM	TYPICAL	MAXIMUM	UNITS
V_B	I_R = 10 μA		70			V
C_T	V_R = 4.0 V	f = 1.0 MHz	44.65	47.0	49.35	pF
ΔC_T	C_{T0}/C_{T60}	f = 1.0 MHz	7.4			---
ΔC_T	C_{T8}/C_{T60}	f = 1.0 MHz	2.50		2.60	---
Q	V_R = 4.0 V	f = 50 MHz	600			---

Specifications are subject to change without notice.